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U.S. UTILITY Patent Application

O.I.P.E. SCANNED

PATENT DATE

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Sei-Hyung Ryu Anant Agarwal Mrinal Das Lori Lipkin				-

Silicon carbide power metal-oxide semiconductor field effect transistors having a shorting channel and methods of fabricating silicon carbide metal-oxide semiconductor field effect transistors having a shorting channel

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TERMINAL	DRAWINGS			CLAIMS ALLOWED		
DISCLAIMEN	Sheets Drwg.	Figs. Drwg.	Print Fig.	Total Claims	Print Claim for O.G.	
The term of this patent subsequent to (date)				NOTICE OF ALL	OWANCE MAILED	
has been disclaimed. The term of this patent shall not extend beyond the expiration date	(Assistent Examiner) (Osto)					
of U.S Patent. No.			ISSUE FEE			
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